BB302C

Build in Biasing Circuit MOS FET IC
VHF RF Amplifier

HITACHI

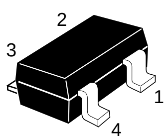
ADE-208-573 A (Z)
2nd. Edition
September 1997

Features

- Build in Biasing Circuit; To reduce using parts cost & PC board space.
- Low noise characteristics;
  (NF = 1.7 dB typ. at f = 200 MHz)
- Withstanding to ESD;
  Build in ESD absorbing diode. Withstand up to 240V at C=200pF, Rs=0 conditions.
- Provide mini mold packages; CMPAK-4(SOT-343mod)

Outline

CMPAK-4



1. Source
2. Gate1
3. Gate2
4. Drain

- Note 1 Marking is “BW–”.
- Note 2 BB302C is individual type number of HITACHI BBFET.

Absolute Maximum Ratings (Ta = 25°C)

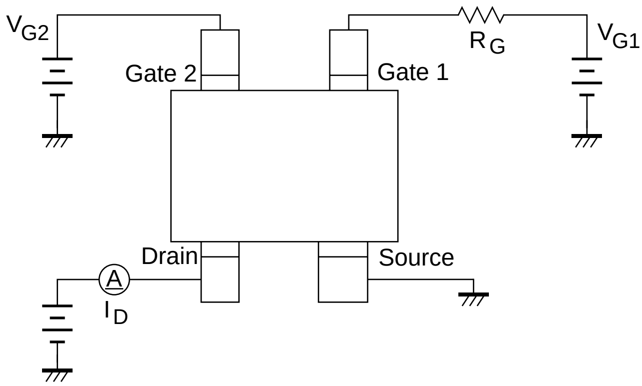
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	12	V
Gate1 to source voltage	V_{G1S}	+10 – 0	V
Gate2 to source voltage	V_{G2S}	±10	V
Drain current	I_D	25	mA
Channel power dissipation	Pch	100	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Electrical Characteristics (Ta = 25°C)

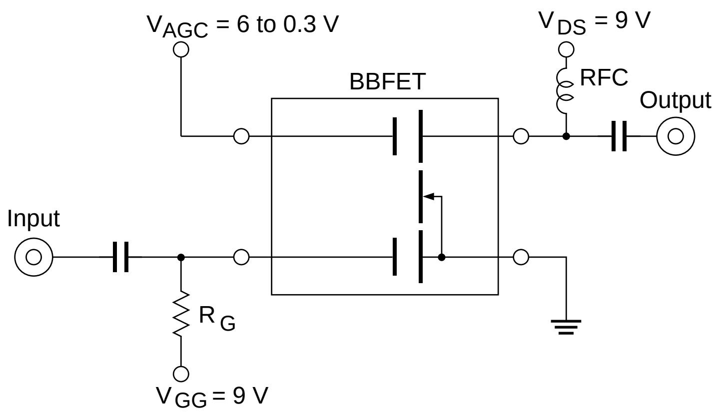
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	12	—	—	V	I_D = 200μA V_{G1S} = V_{G2S} = 0
Gate1 to source breakdown voltage	$V_{(BR)G1SS}$	+10	—	—	V	I_{G1} = +10μA V_{G2S} = V_{DS} = 0
Gate2 to source breakdown voltage	$V_{(BR)G2SS}$	±10	—	—	V	I_{G2} = ±10μA V_{G1S} = V_{DS} = 0
Gate1 to source cutoff current	I_{G1SS}	—	—	+100	nA	V_{G1S} = +9V V_{G2S} = V_{DS} = 0
Gate2 to source cutoff current	I_{G2SS}	—	—	±100	nA	V_{G2S} = ±9V V_{G1S} = V_{DS} = 0
Gate1 to source cutoff voltage	$V_{G1S(off)}$	0.4	—	1.0	V	V_{DS} = 9V, V_{G2S} = 6V I_D = 100μA
Gate2 to source cutoff voltage	$V_{G2S(off)}$	0.4	—	1.0	V	V_{DS} = 9V, V_{G1S} = 9V I_D = 100μA
Drain current	$I_{D(op)}$	9	13	18	mA	V_{DS} = 9V, V_{G1} = 9V V_{G2S} = 6V R_G = 120kΩ
Forward transfer admittance	$\|y_{fs}\|$	15	20	—	mS	V_{DS} = 9V, V_{G1} = 9V V_{G2S} =6V R_G = 120kΩ, f = 1kHz
Input capacitance	c_{iss}	2.2	3.0	4.0	pF	V_{DS} = 9V, V_{G1} = 9V
Output capacitance	c_{oss}	0.8	1.1	1.5	pF	V_{G2S} =6V, R_G = 120kΩ
Reverse transfer capacitance	c_{rss}	—	0.017	0.04	pF	f = 1MHz
Power gain	PG	22	26	—	dB	V_{DS} = 9V, V_{G1} = 9V V_{G2S} =6V
Noise figure	NF	—	1.7	2.2	dB	R_G = 120kΩ f = 200MHz

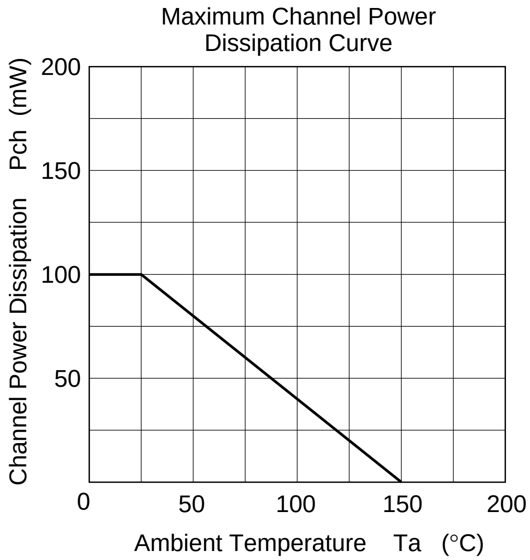
Main Characteristics

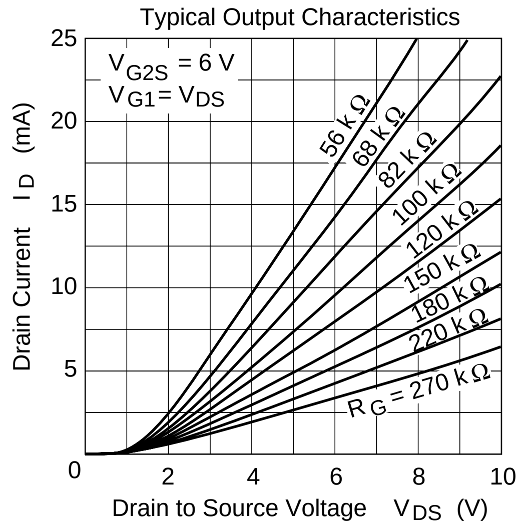
Test Circuit for Operating Items ($I_{D(op)}$, |yfs|, Ciss, Coss, Crss, NF, PG)

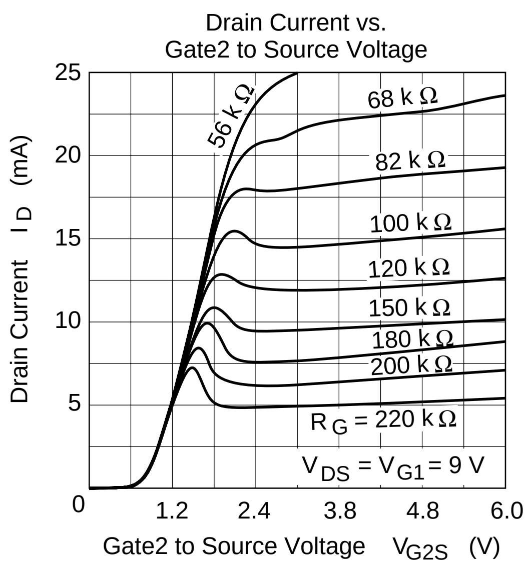


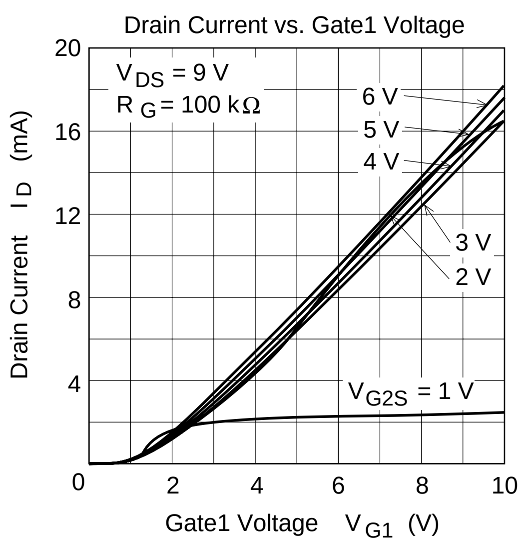
Application Circuit

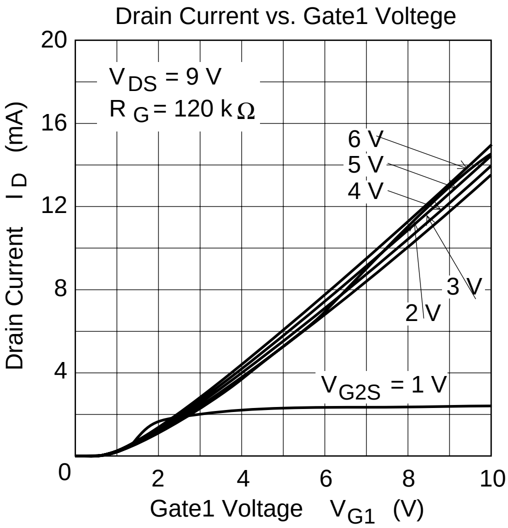


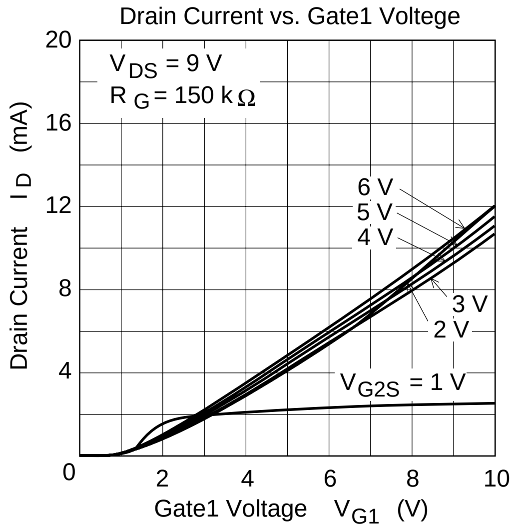

Maximum Channel Power
Dissipation Curve
Channel Power Dissipation Pch (mW)
200
150
100
50
0
50
100
150
200
Ambient Temperature Ta (°C)

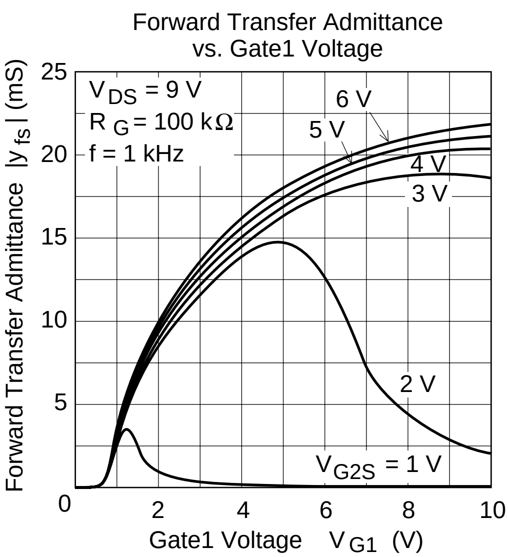

Typical Output Characteristics
V G2S = 6 V
V G1 = V DS
56 k Ω
68 k Ω
82 k Ω
100 k Ω
120 k Ω
150 k Ω
180 k Ω
220 k Ω
R G = 270 k Ω
Drain Current I D (mA)
25
20
15
10
5
0
2
4
6
8
10
Drain to Source Voltage V DS (V)

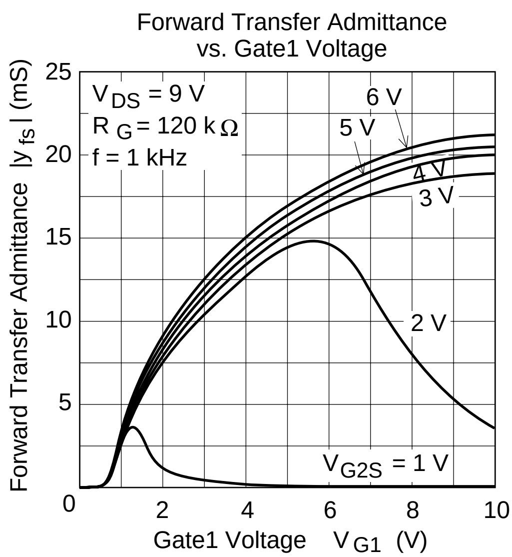

Drain Current vs.
Gate2 to Source Voltage
56 k Ω
68 k Ω
82 k Ω
100 k Ω
120 k Ω
150 k Ω
180 k Ω
200 k Ω
R G = 220 k Ω
V DS = V G1 = 9 V
Drain Current I D (mA)
25
20
15
10
5
0
1.2
2.4
3.8
4.8
6.0
Gate2 to Source Voltage V G2S (V)

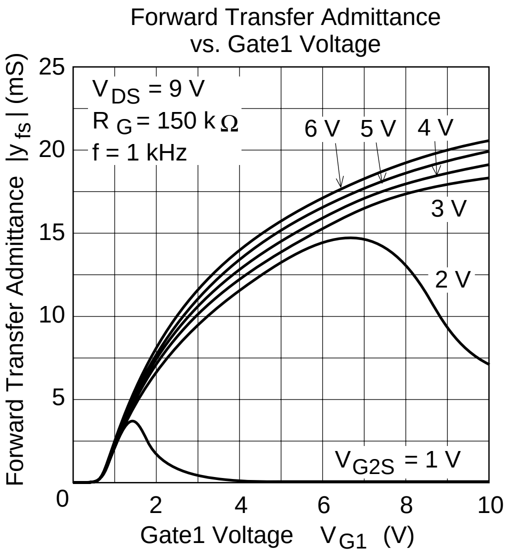

Drain Current vs. Gate1 Voltage
V DS = 9 V
R G = 100 kΩ
6 V
5 V
4 V
3 V
2 V
V G2S = 1 V
Drain Current I D (mA)
20
16
12
8
4
0
2
4
6
8
10
Gate1 Voltage V G1 (V)

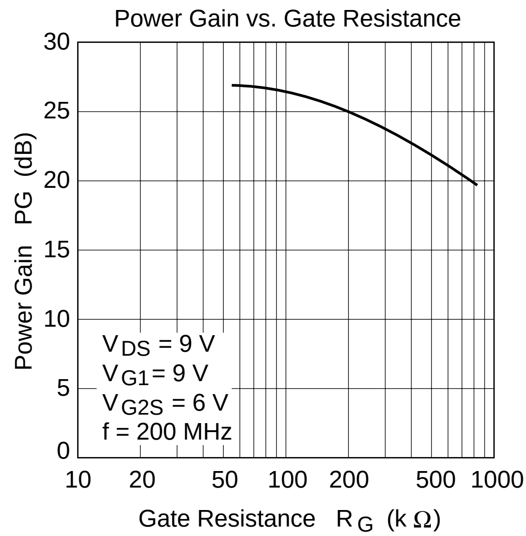

Drain Current vs. Gate1 Voltege
V_{DS} = 9 V
R_G = 120 kΩ
6 V
5 V
4 V
3 V
2 V
V_{G2S} = 1 V
Drain Current I_D (mA)
Gate1 Voltage V_{G1} (V)
0
2
4
6
8
10
4
8
12
16
20

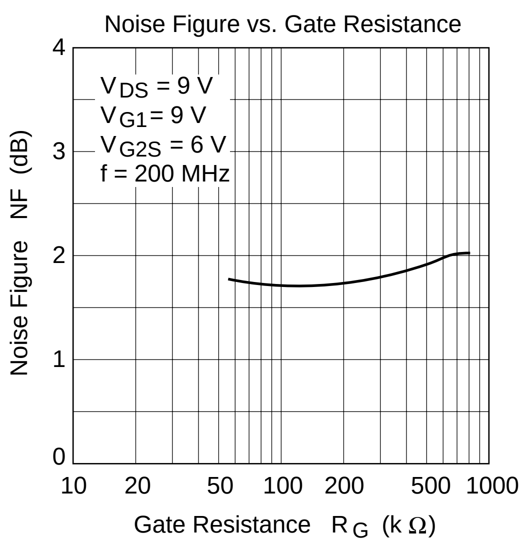

Drain Current vs. Gate1 Voltege
V_{DS} = 9 V
R_G = 150 kΩ
6 V
5 V
4 V
3 V
2 V
V_{G2S} = 1 V
Drain Current I_D (mA)
Gate1 Voltage V_{G1} (V)
0
2
4
6
8
10
4
8
12
16
20

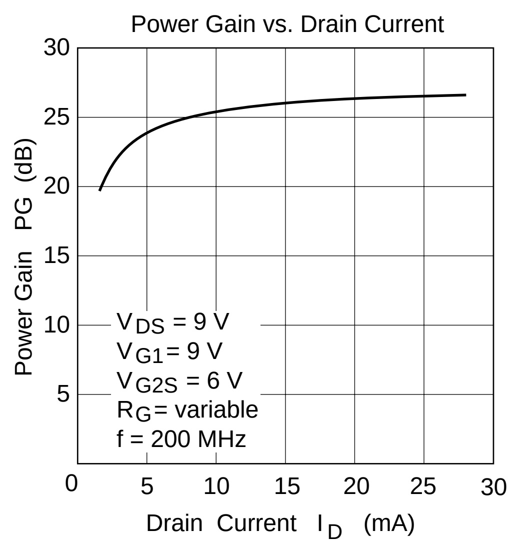

Forward Transfer Admittance
vs. Gate1 Voltage
V_{DS} = 9 V
R_G = 100 kΩ
f = 1 kHz
6 V
5 V
4 V
3 V
2 V
V_{G2S} = 1 V
Forward Transfer Admittance $|y_{fs}|$ (mS)
Gate1 Voltage V_{G1} (V)
0
2
4
6
8
10
5
10
15
20
25

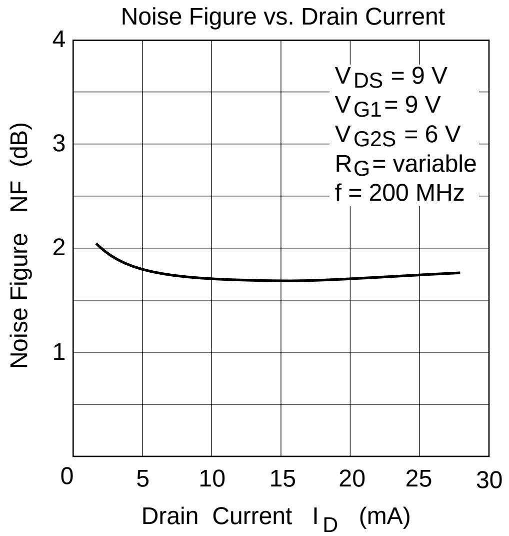

Forward Transfer Admittance
vs. Gate1 Voltage
V_{DS} = 9 V
R_G = 120 kΩ
f = 1 kHz
6 V
5 V
4 V
3 V
2 V
V_{G2S} = 1 V
Forward Transfer Admittance $|y_{fs}|$ (mS)
Gate1 Voltage V_{G1} (V)
0
2
4
6
8
10
5
10
15
20
25

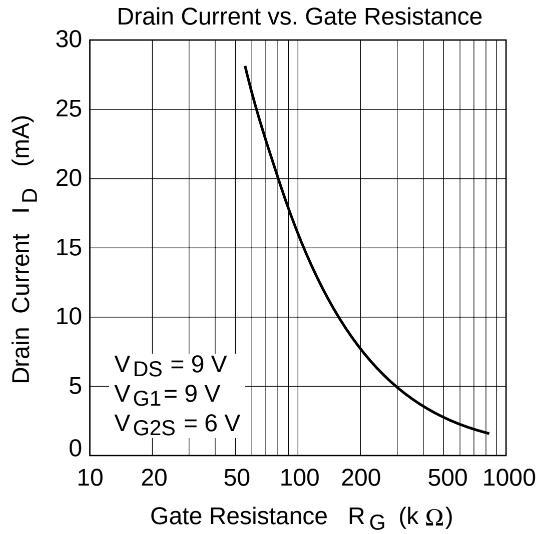

Forward Transfer Admittance
vs. Gate1 Voltage
Forward Transfer Admittance |y fs| (mS)
Gate1 Voltage V G1 (V)
V DS = 9 V
R G = 150 k Ω
f = 1 kHz
6 V
5 V
4 V
3 V
2 V
V G2S = 1 V
0
5
10
15
20
25
2
4
6
8
10

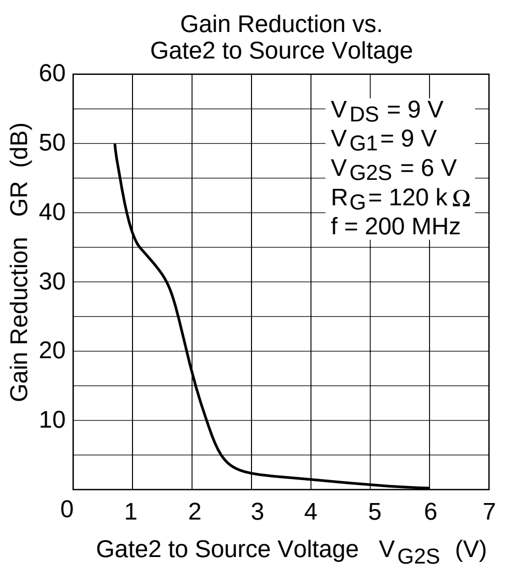

Power Gain vs. Gate Resistance
Power Gain PG (dB)
Gate Resistance R G (k Ω)
V DS = 9 V
V G1 = 9 V
V G2S = 6 V
f = 200 MHz
0
5
10
15
20
25
30
10
20
50
100
200
500
1000

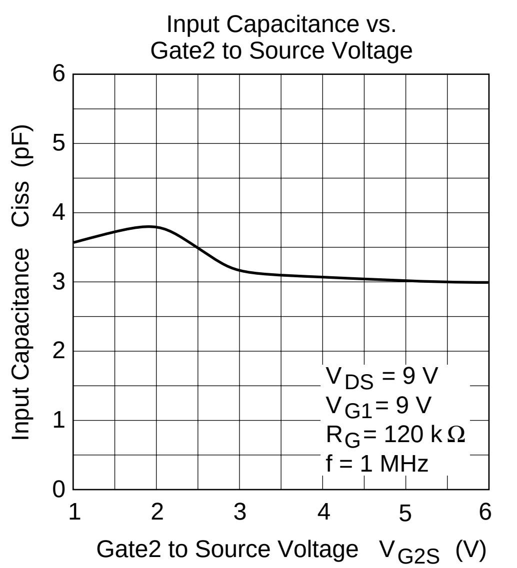

Noise Figure vs. Gate Resistance
Noise Figure NF (dB)
Gate Resistance R G (k Ω)
V DS = 9 V
V G1 = 9 V
V G2S = 6 V
f = 200 MHz
0
1
2
3
4
10
20
50
100
200
500
1000


Power Gain vs. Drain Current
Power Gain PG (dB)
Drain Current I D (mA)
V DS = 9 V
V G1 = 9 V
V G2S = 6 V
R G = variable
f = 200 MHz
0
5
10
15
20
25
30
5
10
15
20
25
30

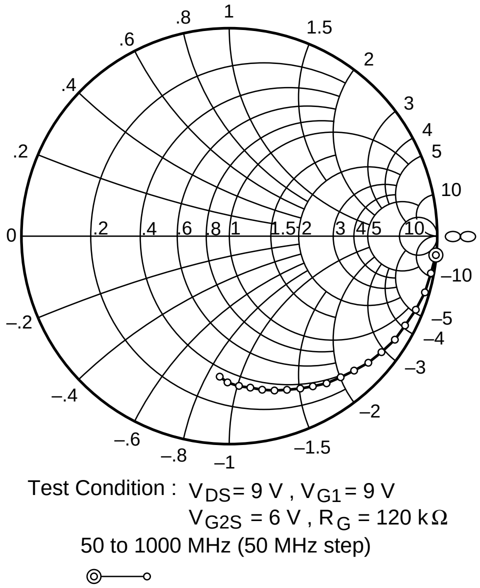

Noise Figure vs. Drain Current
Noise Figure NF (dB)
Drain Current I D (mA)
V DS = 9 V
V G1 = 9 V
V G2S = 6 V
R G = variable
f = 200 MHz
0
1
2
3
4
5
10
15
20
25
30


Drain Current vs. Gate Resistance
Drain Current I D (mA)
Gate Resistance R G (k Ω)
V DS = 9 V
V G1 = 9 V
V G2S = 6 V
0
5
10
15
20
25
30
10
20
50
100
200
500
1000


Gain Reduction vs.
Gate2 to Source Voltage
Gain Reduction GR (dB)
Gate2 to Source Voltage V G2S (V)
V DS = 9 V
V G1 = 9 V
V G2S = 6 V
R G = 120 k Ω
f = 200 MHz
0
10
20
30
40
50
60
1
2
3
4
5
6
7

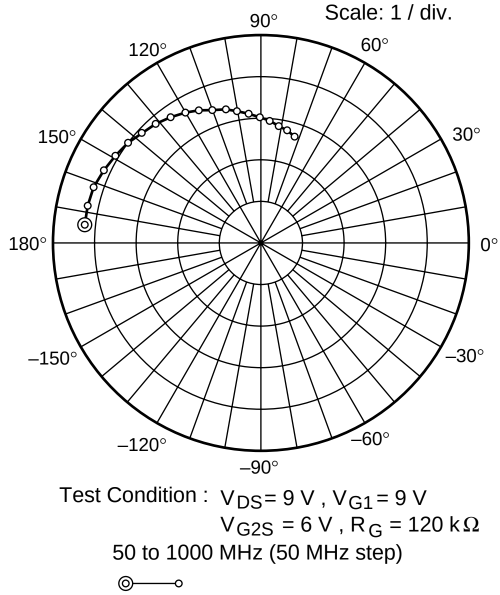

Input Capacitance vs.
Gate2 to Source Voltage
Input Capacitance Ciss (pF)
Gate2 to Source Voltage V G2S (V)
V DS = 9 V
V G1 = 9 V
R G = 120 k Ω
f = 1 MHz
0
1
2
3
4
5
6
1
2
3
4
5
6

S11 Parameter vs. Frequency



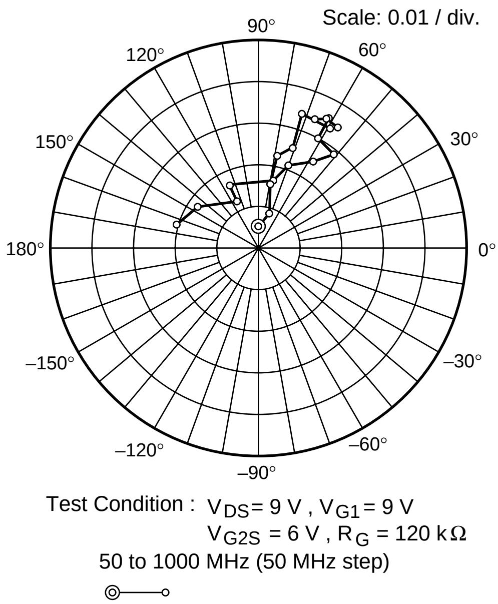
Test Condition : V_{DS} = 9 V , V_{G1} = 9 V
V_{G2S} = 6 V , R_G = 120 kΩ
50 to 1000 MHz (50 MHz step)

S21 Parameter vs. Frequency



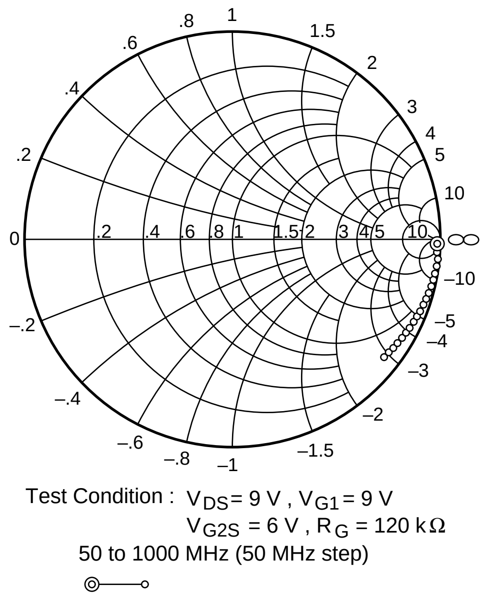
Test Condition : V_{DS} = 9 V , V_{G1} = 9 V
V_{G2S} = 6 V , R_G = 120 kΩ
50 to 1000 MHz (50 MHz step)

S12 Parameter vs. Frequency



Test Condition : V_{DS} = 9 V , V_{G1} = 9 V
V_{G2S} = 6 V , R_G = 120 kΩ
50 to 1000 MHz (50 MHz step)

S22 Parameter vs. Frequency



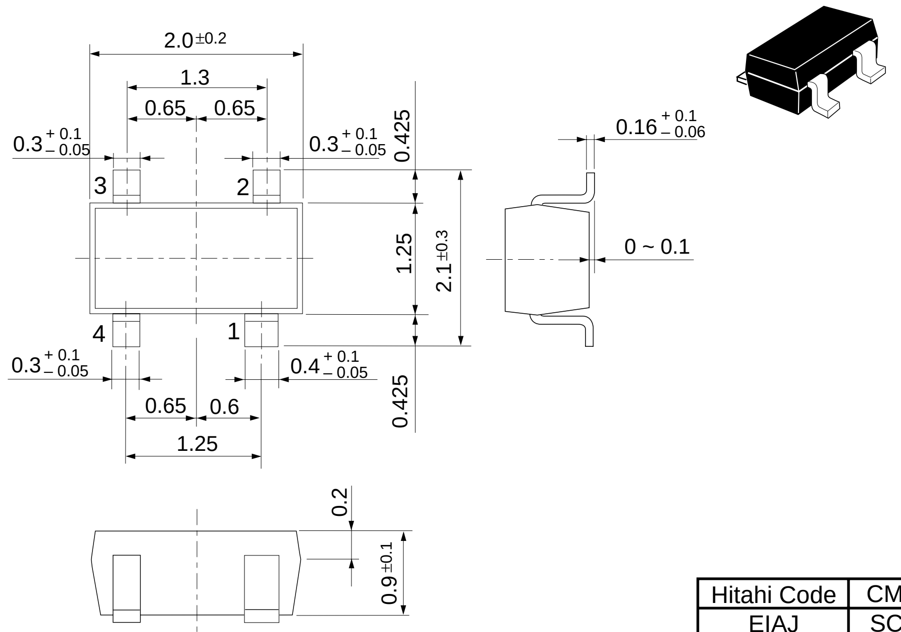
Test Condition : V_{DS} = 9 V , V_{G1} = 9 V
V_{G2S} = 6 V , R_G = 120 kΩ
50 to 1000 MHz (50 MHz step)

Sparameter ($V_{DS} = V_{G1} = 9V$, $V_{G2S} = 6V$, $R_G = 120k\Omega$, $Zo = 50\Omega$)

	S11		S21		S12		S22	
f (MHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
50	0.988	–5.2	2.13	174.1	0.00052	90.0	0.985	–1.3
100	0.986	–10.4	2.13	167.9	0.00087	72.5	0.993	–3.6
150	0.979	–16.0	2.12	161.6	0.00156	79.4	0.992	–5.5
200	0.964	–21.5	2.08	155.2	0.00226	78.4	0.990	–7.5
250	0.948	–26.9	2.04	149.1	0.00254	71.0	0.987	–9.6
300	0.939	–32.0	2.00	143.0	0.00339	72.0	0.985	–11.4
350	0.920	–37.3	1.95	137.3	0.00335	59.0	0.982	–13.3
400	0.904	–42.3	1.91	131.5	0.00338	66.3	0.978	–15.3
450	0.885	–47.1	1.86	125.7	0.00351	62.2	0.974	–17.1
500	0.864	–51.7	1.81	120.1	0.00347	56.6	0.970	–18.9
550	0.848	–56.5	1.76	115.1	0.00355	61.5	0.966	–21.0
600	0.826	–60.9	1.70	110.1	0.00300	61.4	0.961	–22.7
650	0.808	–65.0	1.66	104.7	0.00289	51.1	0.957	–24.5
700	0.789	–69.4	1.61	100.3	0.00246	57.6	0.952	–26.6
750	0.773	–73.7	1.56	95.4	0.00211	70.0	0.947	–28.3
800	0.755	–77.9	1.51	90.5	0.00166	77.5	0.943	–30.2
850	0.735	–82.1	1.47	85.9	0.00165	114.5	0.937	–32.2
900	0.721	–86.3	1.42	81.3	0.00123	114.5	0.933	–34.1
950	0.703	–90.7	1.39	76.9	0.00176	145.8	0.927	–35.9
1000	0.677	–93.9	1.34	72.4	0.00204	164.0	0.923	–37.9

Package Dimensions

Unit: mm



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